

CMOS Power

Outline

- ☐ Power and Energy
- ☐ Dynamic Power
- ☐ Static Power

Power and Energy

❑ Power is drawn from a voltage source attached to the V_{DD} pin(s) of a chip.

❑ Instantaneous Power: $P(t) = I(t)V(t)$

❑ Energy:
$$E = \int_0^T P(t)dt$$

❑ Average Power:
$$P_{\text{avg}} = \frac{E}{T} = \frac{1}{T} \int_0^T P(t)dt$$

Power in Circuit Elements

$$P_{VDD}(t) = I_{DD}(t)V_{DD}$$



$$P_R(t) = \frac{V_R^2(t)}{R} = I_R^2(t)R$$



$$\begin{aligned} E_C &= \int_0^{\infty} I(t)V(t)dt = \int_0^{\infty} C \frac{dV}{dt} V(t)dt \\ &= C \int_0^{V_C} V(t)dV = \frac{1}{2} CV_C^2 \end{aligned}$$



Charging a Capacitor

- When the gate output rises
 - Energy stored in capacitor is

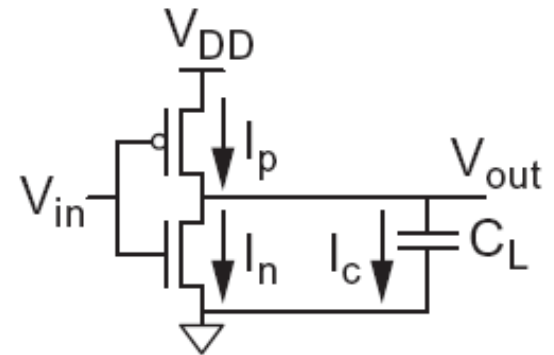
$$E_C = \frac{1}{2} C_L V_{DD}^2$$

- But energy drawn from the supply is

$$\begin{aligned} E_{VDD} &= \int_0^\infty I(t) V_{DD} dt = \int_0^\infty C_L \frac{dV}{dt} V_{DD} dt \\ &= C_L V_{DD} \int_0^{V_{DD}} dV = C_L V_{DD}^2 \end{aligned}$$

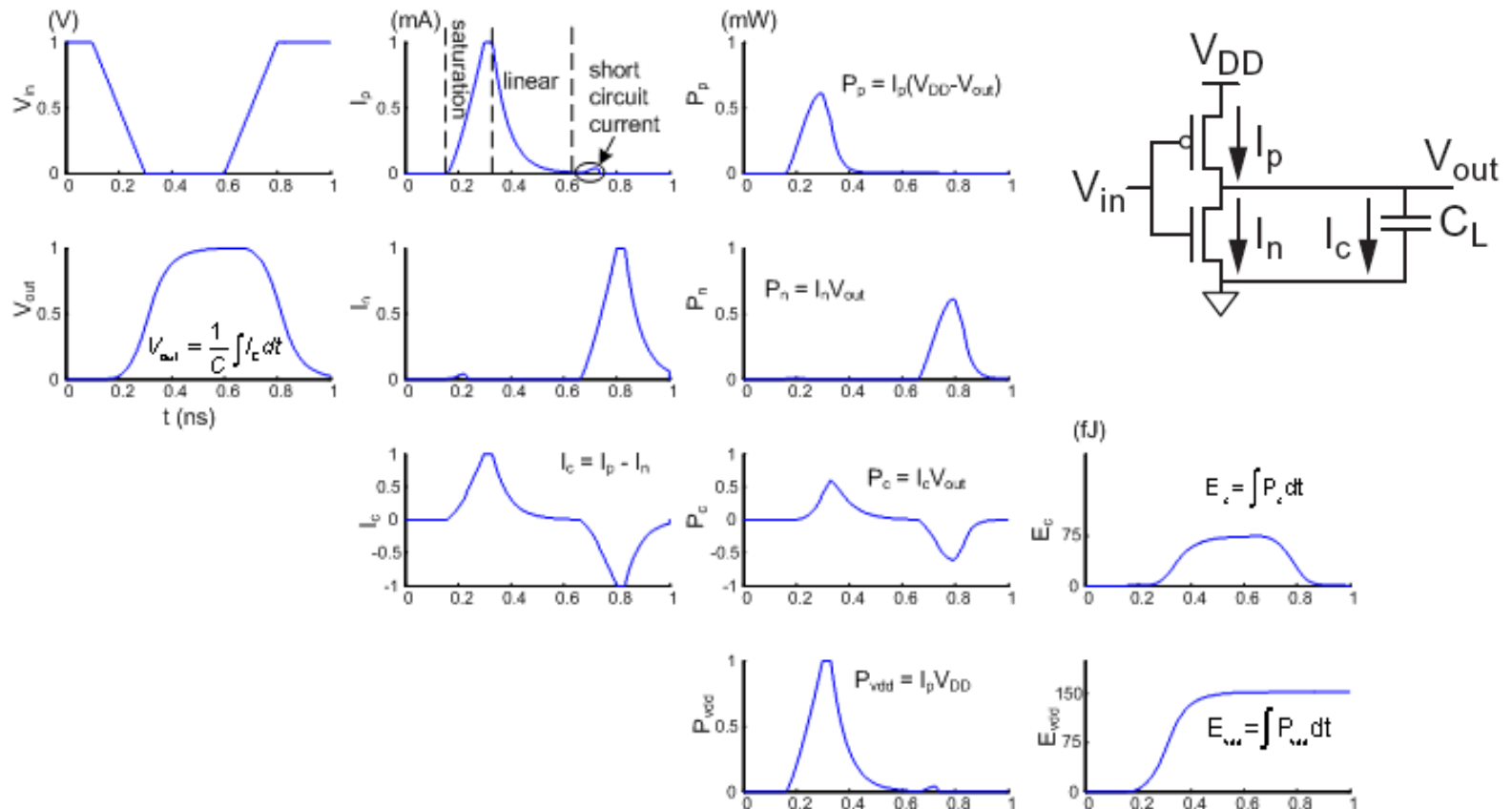
- Half the energy from V_{DD} is dissipated in the pMOS transistor as heat, other half stored in capacitor

- When the gate output falls
 - Energy in capacitor is dumped to GND
 - Dissipated as heat in the nMOS transistor



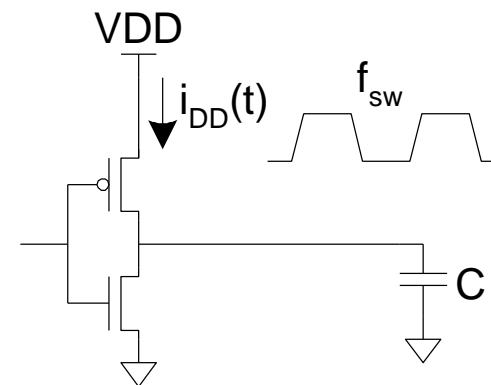
Switching Waveforms

□ Example: $V_{DD} = 1.0 \text{ V}$, $C_L = 150 \text{ fF}$, $f = 1 \text{ GHz}$



Switching Power

$$\begin{aligned} P_{\text{switching}} &= \frac{1}{T} \int_0^T i_{DD}(t) V_{DD} dt \\ &= \frac{V_{DD}}{T} \int_0^T i_{DD}(t) dt \\ &= \frac{V_{DD}}{T} [T f_{\text{sw}} C V_{DD}] \\ &= C V_{DD}^2 f_{\text{sw}} \end{aligned}$$



Activity Factor

- ❑ Suppose the system clock frequency = f
- ❑ Let $f_{sw} = \alpha f$, where α = activity factor
 - If the signal is a clock, $\alpha = 1$
 - If the signal switches once per cycle, $\alpha = 1/2$

- ❑ Dynamic power:

$$P_{\text{switching}} = \alpha C V_{DD}^2 f$$

Short Circuit Current

- ❑ When transistors switch, both nMOS and pMOS networks may be momentarily ON at once
- ❑ Leads to a blip of “short circuit” current.
- ❑ $< 10\%$ of dynamic power if rise/fall times are comparable for input and output
- ❑ We will generally ignore this component

Power Dissipation Sources

- ❑ $P_{\text{total}} = P_{\text{dynamic}} + P_{\text{static}}$
- ❑ Dynamic power: $P_{\text{dynamic}} = P_{\text{switching}} + P_{\text{shortcircuit}}$
 - Switching load capacitances
 - Short-circuit current
- ❑ Static power: $P_{\text{static}} = (I_{\text{sub}} + I_{\text{gate}} + I_{\text{junct}} + I_{\text{contention}})V_{\text{DD}}$
 - Subthreshold leakage
 - Gate leakage
 - Junction leakage
 - Contention current

Dynamic Power Example

- ❑ 1 billion transistor chip
 - 50M logic transistors
 - Average width: 12λ
 - Activity factor = 0.1
 - 950M memory transistors
 - Average width: 4λ
 - Activity factor = 0.02
 - 1.0 V 65 nm process
 - $C = 1 \text{ fF}/\mu\text{m}$ (gate) + $0.8 \text{ fF}/\mu\text{m}$ (diffusion)
- ❑ Estimate dynamic power consumption @ 1 GHz.
Neglect wire capacitance and short-circuit current.

Solution

$$C_{\text{logic}} = (50 \times 10^6)(12\lambda)(0.025 \mu\text{m} / \lambda)(1.8 \text{ fF} / \mu\text{m}) = 27 \text{ nF}$$

$$C_{\text{mem}} = (950 \times 10^6)(4\lambda)(0.025 \mu\text{m} / \lambda)(1.8 \text{ fF} / \mu\text{m}) = 171 \text{ nF}$$

$$P_{\text{dynamic}} = [0.1C_{\text{logic}} + 0.02C_{\text{mem}}](1.0)^2 (1.0 \text{ GHz}) = 6.1 \text{ W}$$

Dynamic Power Reduction

- ❑ $P_{\text{switching}} = \alpha C V_{DD}^2 f$
- ❑ Try to minimize:
 - Activity factor
 - Capacitance
 - Supply voltage
 - Frequency